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### AMENDMENTS TO THE CLAIMS

12. (Original) An SDT junction of a memory cell for an MRAM device, the junction comprising:

a bottom ferromagnetic layer, the bottom ferromagnetic layer having flattened peaks;

an insulating tunnel barrier atop the bottom ferromagnetic layer; and a top ferromagnetic layer atop the insulating tunnel barrier.

13. (Original) The junction of claim 12, wherein angle from the top of a grain to an intersection with an adjacent grain is between about three and six degrees.

14. (Original) The junction of claim 12, wherein the flattened peaks have a valley-to-peak height difference of no more than about one nanometer.

15. (Original) The junction of claim 12, wherein the junction has a resistance of less than about  $10 \text{ K}\Omega\cdot\mu\text{m}^2$ .

16. (Original) The junction of claim 12, wherein the top and bottom layers are AF coupled; wherein the peaks are flattened to tune the AF coupling to a desired level.

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17. (Currently amended) An MRAM device comprising:  
an array of memory cells, each memory cell including an SDT junction,  
each SDT junction including a bottom ferromagnetic layer, each bottom  
ferromagnetic layer having an upper surface, each upper surface having a valley-  
to-peak height variation of no more than about one nanometer;  
a plurality of word lines extending along memory cell rows of the array; and  
a plurality of bit lines extending along memory cell columns of the array.

b  
end  
18. (Original) The device of claim 17, wherein resistance variation of the  
junctions across the entire array is no more than about 4%.

19. (Original) The device of claim 17, wherein angle from the top of a grain  
to an intersection with an adjacent grain is between and three and six degrees.

20. (Original) The device of claim 17, wherein the junctions have a  
resistance of less than about  $10 \text{ K}\Omega\text{-}\mu\text{m}^2$ .

21. (New) An SDT junction comprising:  
a bottom ferromagnetic layer having physically altered peaks;  
an insulating tunnel barrier atop the bottom ferromagnetic layer; and  
a top ferromagnetic layer atop the insulating tunnel barrier.

22. (New) The device of claim 21, wherein the physically altered peaks  
are flattened.